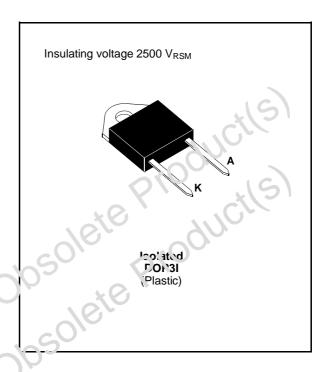


# **BYT 30PI-1000**

## FAST RECOVERY RECTIFIER DIODE

- VERY HIGH REVERSE VOLTAGE CAPABILITY
- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- INSULATED: Capacitance 15pF



#### **SUITABLE APPLICATIONS**

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

#### ABSOLUTE MAXIMUM RAT: NGS, (limiting values,

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetiti 'e Peak Reverse Vc'ta, re	1000	V	
V <sub>RSM</sub>	Non Repetitive Peak Reverse Voltage	1000	V	
I <sub>F′</sub> ⟨M	Repetive Peak To ward Current t <sub>p</sub> ≤ 10µs		375	Α
IF ("(MS)	RMS Forv and Current	70	Α	
I <sub>F (AV)</sub>	A\ er⊿ge Forward Current	$T_c = 50^{\circ}C$ $\delta = 0.5$	30	А
I <sub>Fξ M</sub>	Surge non Repetitive Forward Current	t <sub>p</sub> = 10ms Sinusoidal	200	А
Р	Power Dissipation	T <sub>c</sub> = 50°C	60	W
T <sub>stg</sub>	Storage and Junction Temperature Range	- 40 to +150	°C	

#### THERMAL RESISTANCE

ĺ	Symbol	Parameter	Value	Unit
	R <sub>th (j - c)</sub>	Junction-case	1.6	°C/W

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#### **ELECTRICAL CHARACTERISTICS**

#### STATIC CHARACTERISTICS

Synbol	Test Conditions			Тур.	Max.	Unit
I <sub>R</sub>	T <sub>j</sub> = 25°C	$V_R = V_{RRM}$			100	μΑ
	T <sub>j</sub> = 100°C				5	mA
V <sub>F</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 30A			1.9	V
	T <sub>j</sub> = 100°C				1.8	

#### RECOVERY CHARACTERISTICS

Ī	Symbol		Test Co	nditions		Min.	Тур.	Max.	L'nit
	t <sub>rr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A	$di_F/dt = -15A/\mu s$	V <sub>R</sub> = 30V		. (	'6 <del>ເ</del>	ns
			I <sub>F</sub> = 0.5A	I <sub>R</sub> = 1A	$I_{rr} = 0.25A$		7101	70	

## TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol	Test Conditions		Min.	Тур.	Max.	Unit
t <sub>IRM</sub>	di <sub>F</sub> /dt = - 120A/μs	V <sub>CC</sub> = 200 V I <sub>F</sub> = 30A			200	ns
	di <sub>F</sub> /dt = - 240A/μs	$L_p \le 0.05 \mu H$ $T_j = 100^{\circ} C$ See figure 11		120		
I <sub>RM</sub>	di <sub>F</sub> /dt = -120A/μs	003			19.5	Α
	$di_F/dt = -240A/\mu s$			22		

### TURN-OFF OVERVOLTAGE COEFFICIEN (With Series Inductance)

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$			4.5	

To evaluate the conduction losses use the following equations:

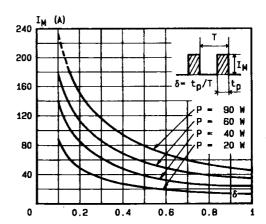
$$V_F = 1.47 \text{ }^{\circ} \text{ } ?.?10 \text{ } I_F$$
  $P = 1.47 \text{ } x \text{ } I_{F(AV)} + 0.010 \text{ } I_F^2_{(RMS)}$ 

-0/6

20 10 15 20 25 30

Figure 1. Low frequency power losses versus

Figure 2. Peak current versus form factor



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Figure 3. Non repetitive peak surge current versus overload duration

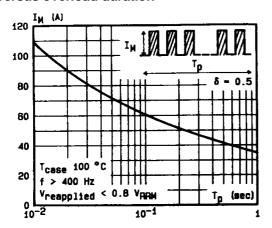


Figure 4. Thermal impedance versus pulse width

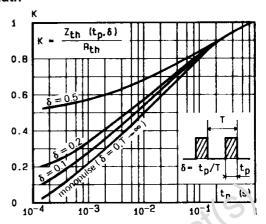


Figure 5. Voltage drop versus forward current

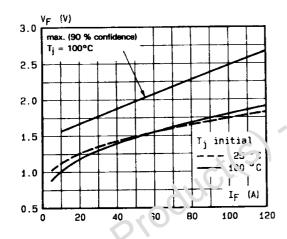


Figure 6. Recovery chalge versus dir/dt-

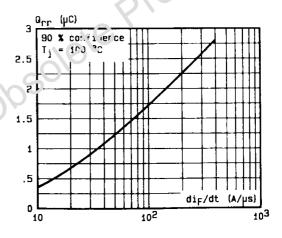


Figure 7. Recovery time versus dir/dt-

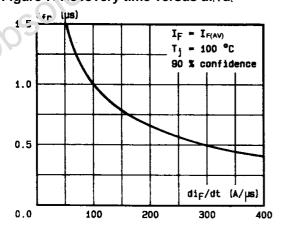
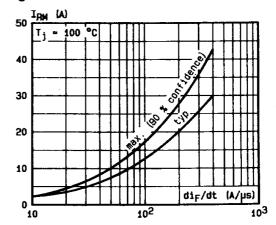


Figure 8. Peak reverse current versus dir/dt-



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Figure 9. Peak forward voltage versus di<sub>F</sub>/d<sub>t-</sub>

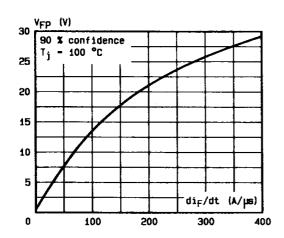


Figure 10. Dynamic parameters versus junction temperature.

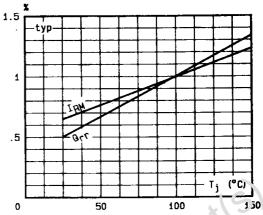


Figure 11. Turn-off switching characteristics (without series inductance).

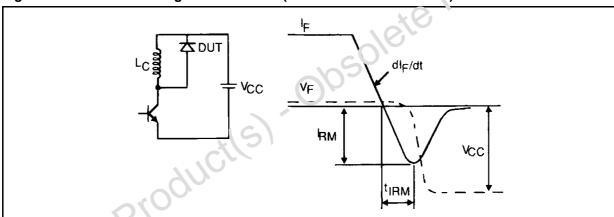
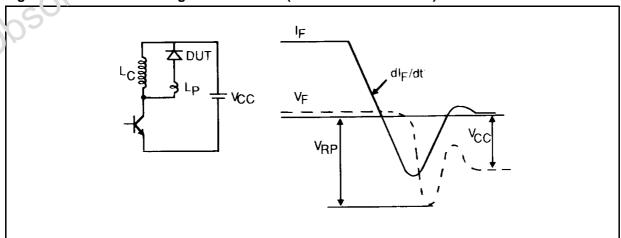


Figure 12. Turn-off switching characteristics (with series inductance)



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**Inches** 

Max.

0.181

0.061

0.614

0.028

0.114

ú.r.51)

0.831

0.610

0.144

0.164

0.444

0.055

Min.

0.173

0.057

0.565

0.020

0.106

0.622

0.8(5

C 594

0.134

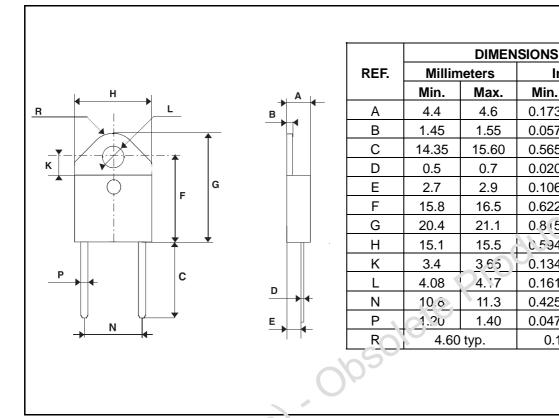
0.161

0.425

0.047

0.181 typ.

#### PACKAGE MECHANICAL DATA: Isolated DOP3I Plastic



Cooling method: by conduction (method C) Marking: type number Weight: 18.84g Recommended torque value: 250cm. N Maximum torque value: 310cm. N

obsolete P'

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